

# High Efficiency SuperCap Charger for Photovoltaic Sources

#### DESCRIPTION

The TS52003 is a DC/DC synchronous switching Super Capacitor Charger with fully integrated power switches, internal compensation, and full fault protection. The TS52003 utilizes a temperature-independent photovoltaic Maximum Power Point Tracking (MPPT-Lite<sup>TM</sup>) calculator to optimize power output from the source during Full-Charge mode. The switching frequency of 1MHz enables the use of small filter components, which result in smaller board space and reduced BOM costs.

In Full-Charge mode the duty cycle is controlled by the MPPT-Lite<sup>TM</sup> regulator. Once termination voltage is reached, the regulator operates in voltage mode. When the regulator is disabled (EN is low), the device draws 10uA quiescent current.

The TS52003 integrates a wide range of protection circuitry; including input supply under-voltage lockout, output over-voltage protection, current limit, and thermal shutdown.

The TS52003 includes supervisory reporting through the nFLT (Inverted Fault) open drain output to interface other components in the system. Device programming is achieved by an I<sup>2</sup>C interface through SCL and SDA pins.

#### **FEATURES**

- Utilizes a temperature-independent PV MPPT-Lite<sup>TM</sup> regulation scheme
- VOUT reverse current blocking
- Wide input voltage range: 3.2V to 7.2V
- Up to 1.5A continuous output current
- Programmable temperature-compensated termination voltage with a ± 1% tolerance
- User programmable termination voltage
- High efficiency up to 92% at typical load
- Current mode PWM control in constant voltage
- Input supply under voltage lockout
- Full protection for V<sub>OUT</sub> over-voltage
- Device over-current and over-temperature protection
- I2C program interface with EEPROM registers
- V<sub>OUT</sub> reverse current blocking
- Charge status indication

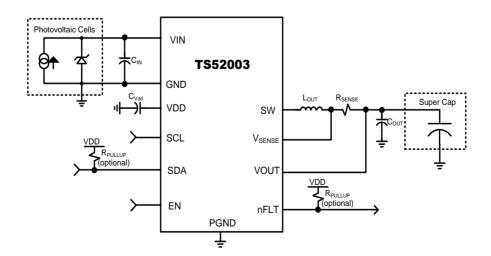
#### SUMMARY SPECIFICATIONS

Packaged in a 16pin QFN (4x4)

#### APPLICATIONS

- Off-grid systems
- Wireless sensor networks
- Smoke detectors
- HVAC controls

### TYPICAL APPLICATION



# **PINOUT**

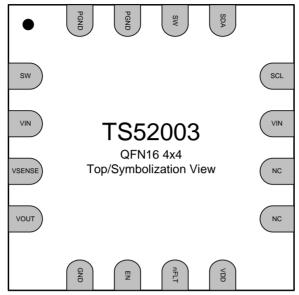


Figure 1b: Package Pinout Diagram

# PIN DESCRIPTION

Pin Symbol	Pin #	Function	Description
SW	1	Switching Voltage Node	Connected to 4.7uH (typical) inductor
VIN	2	Photovoltaic Input Voltage	Input voltage
VSENSE	3	Current Sense Positive Input	Positive input for the MPP current loop.
VOUT	4	Super Cap Voltage	Regulator Feedback Input
GND	5	GND	Primary ground for the majority of the device except the low-side power FET.
EN	6	Enable Input	Above 2.2V the device is enabled. GND the pin to disable the device. Includes internal pull-up.
nFLT	7	Inverted Fault	Open-drain output.
VDD	8	Internal 3.3V Supply Output	Connected to 100nF capacitor to GND
	9	Unused	GND in application
	10	Unused	GND in application
VIN	11	Photovoltaic Input Voltage	Input voltage
SCL	12	Clock Input	I <sup>2</sup> C clock input.
SDA	13	Data Input/Output	I <sup>2</sup> C data open-drain output.
SW	14	Switching Voltage Node	Connected to 4.7uH (typical) inductor
PGND	15	Power GND	GND supply for internal low-side FET/integrated diode
PGND	16	Power GND	GND supply for internal low-side FET/integrated diode

## **FUNCTIONAL BLOCK DIAGRAM**

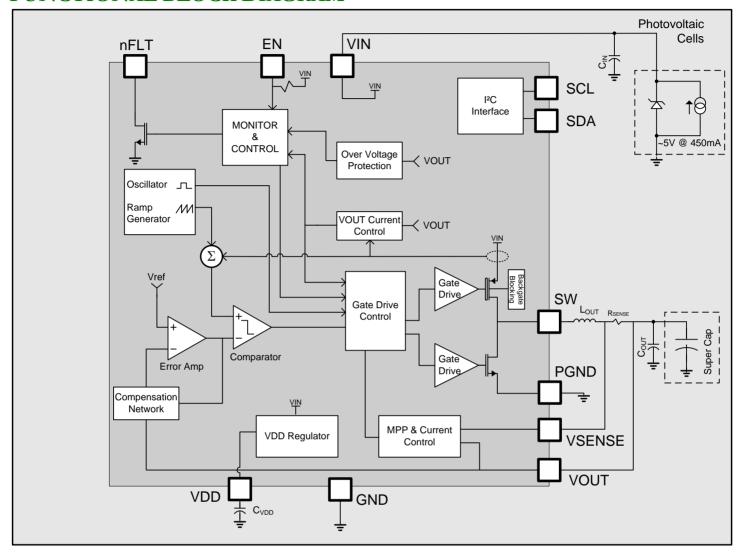


Figure 2: TS52003 Block Diagram



#### ABSOLUTE MAXIMUM RATINGS

Over operating free-air temperature range unless otherwise noted<sup>(1,2,3)</sup>

Parameter	Range	Unit
VIN, EN, nFLT, SCL, SDA, VOUT, VSENSE	-0.3 to 8	V
SW	-1 to 8.8	V
VDD	-0.3 to 3.6	V
Operating Junction Temperature Range, T <sub>J</sub>	-40 to 125	°C
Storage Temperature Range, T <sub>STG</sub>	-65 to 150	°C
Electrostatic Discharge – Human Body Model	±2k	V
Electrostatic Discharge – Machine Model	+/-200	V
Lead Temperature (soldering, 10 seconds)	260	°C

<sup>(1)</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$\theta_{JA}$	Thermal Resistance Junction to Air (Note 1)	50	°C/W

Note 1: Assumes 4x4 QFN-16 in 1 in² area of 2 oz copper and 25°C ambient temperature.

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Unit
VIN	Photovoltaic Input Operating Voltage	3.2	5.3	7.2	V
R <sub>SENSE</sub>	Sense Resistor		50		mΩ
$L_{OUT}$	Output Filter Inductor Typical Value (Note 1)		4.7		uН
$C_{OUT}$	Output Filter Capacitor Typical Value (Note 2)		4.7		uF
C <sub>OUT-ESR</sub>	Output Filter Capacitor ESR			100	mΩ
$C_{IN}$	Input Supply Bypass Capacitor Typical Value (Note 3)	3.3	10		uF
$C_{\mathrm{VDD}}$	VDD Supply Bypass Capacitor Value (Note 2)	70	100	130	nF
$T_{A}$	Operating Free Air Temperature	-40		85	°C
$T_{J}$	Operating Junction Temperature	-40		125	°C

Note 1: For best performance, an inductor with a saturation current rating higher than the maximum V<sub>OUT</sub> load requirement plus the inductor current ripple.

<sup>(2)</sup> All voltage values are with respect to network ground terminal.

<sup>(3)</sup> ESD testing is performed according to the respective JESD22 JEDEC standard.

Note 2: For best performance, a low ESR ceramic capacitor should be used.

Note 3: For best performance, a low ESR ceramic capacitor should be used. If C<sub>IN</sub> is not a low ESR ceramic capacitor, a 0.1uF ceramic capacitor should be added in parallel to C<sub>IN</sub>.



## **CHARACTERISTICS**

Electrical Characteristics,  $T_1 = -40C$  to 125C, VIN = 5.3V (unless otherwise noted)

Symbol	Parameter Parameter	Min	Тур	Max	Unit	
VIN Supply V	I I	Condition				
VIN	Photovoltaic Voltage Input		3.2	5.3	7.2	V
I <sub>CC-NORM</sub>	Quiescent current Normal Mode	$I_{LOAD} = 0A$		3		mA
I <sub>CC-DISABLE</sub>	Quiescent current Disable Mode	EN = 0V		10	50	uA
VOUT Leaka	ge		·			
I <sub>OUT-LEAK</sub>	Leakage Current	EN = 0V, Vout = 2.7V			10	uA
I <sub>OUT-BACK</sub>	Reverse Current	Vout > VIN, Vout = 2.7V			10	uA
VIN Under-V	oltage Lockout					
VIN <sub>-UV</sub>	Input Supply Under-Voltage Threshold	VIN Increasing		3.15		V
VIN <sub>-UV_HYST</sub>	Input Supply Under-Voltage Threshold Hysteresis		100	200		mV
OSC						
Fosc	Oscillator Frequency		0.9	1	1.1	MHz
nFLT Open D	Prain Output			_		
$T_{nFLT}$	nFLT Release Timer			0		ms
I <sub>OH-nFLT</sub>	High-Level Output Leakage	$V_{nFLT} = 5.3V$		0.1		uA
$V_{\text{OL-nFLT}}$	Low-Level Output Voltage	$I_{nFLT} = -1mA$			0.4	V
EN/SCL/SDA	Input Voltage Thresholds					
$V_{IH}$	High Level Input Voltage		2.2			V
$V_{\rm IL}$	Low Level Input Voltage				0.8	V
$V_{HYST}$	Input Hysteresis			200		mV
I <sub>IN-EN</sub>	Input Leakage	$V_{EN}=VIN$		0.1		uA
IIN-EN	input Leakage	$V_{EN}=0V$		-2.0		uA
I <sub>IN-SCL</sub>	Input Leakage	V <sub>SCL</sub> =VIN		55		uA
IN-SCL	Input Leakage	$V_{SCL}=0V$		-0.1		uA
I <sub>IN-SDA</sub>	Input Leakage —	$V_{SDA}$ =VIN		0.1		uA
		$V_{SDA}=0V$		-0.1		uA
V <sub>OL-SDA</sub>	Low-Level Output Voltage	$I_{SDA} = -1mA$			0.4	V
Thermal Shu				1	1	1
TSD	Thermal Shutdown Junction Temperature		150	170		С
TSD <sub>HYST</sub>	TSD Hysteresis			10		С



### **CHARGER CHARACTERISTICS**

Electrical Characteristics,  $T_1 = -40C$  to 125C, VIN = 5.3V (unless otherwise noted)

Symbol	Parameter	Condition	Min	Тур	Max	Unit			
Charging Regulat	harging Regulator: L=4.7uH and C=4.7uF								
I <sub>OUT-FC</sub>	Output Current Limit in Full-Charge Mode	I <sub>OUT</sub> = 1.5A	I <sub>OUT</sub> - 10%	I <sub>OUT</sub>	I <sub>OUT</sub> + 10%	A			
$V_{\text{OUT}}$	Termination Voltage Tolerance	Termination Voltage Tolerance			V <sub>OUT</sub> + 1%	V			
$t_{FC}$	Full-Charge Timer		200		1400	min			
D	High Side Switch On Resistance	$I_{SW} = -1A, T_{J} = 25C$		250		mΩ			
$R_{DSON}$	Low Side Switch On Resistance	$I_{SW} = 1A, T_J = 25C$		150		mΩ			
$I_{OUT}$	Max Output Current			1.5		Α			
$I_{OCD}$	Over-Current Detect	HS switch current		2.5		Α			
$V_{\text{OUT-OV}}$	V <sub>OUT</sub> Over-Voltage Threshold		101% V <sub>OUT</sub>	102% V <sub>OUT</sub>	103% V <sub>OUT</sub>				
V <sub>OUT-OV_HYST</sub>	V <sub>OUT</sub> Over-Voltage Hysteresis		0.2% V <sub>OUT</sub>	0.4% V <sub>OUT</sub>	0.6% V <sub>OUT</sub>				
DUTY <sub>MAX</sub>	Max Duty Cycle			98		%			

# I<sup>2</sup>C INTERFACE TIMING REQUIREMENTS

Electrical Characteristics,  $T_1 = -40C$  to 125C, VIN = 5.3V (unless otherwise noted)

Cl l	Domonoston	Standa	rd Mode	Fast M	11	
Symbol	Parameter	Min	Max	Min	Max	Unit
$f_{scl}$	I <sup>2</sup> C clock frequency	0	100	0	400	kHz
t <sub>sch</sub>	I <sup>2</sup> C clock high time	4		0.6		μs
$t_{\rm scl}$	I <sup>2</sup> C clock low time	4.7		1.3		μs
t <sub>sp</sub> (2)	I <sup>2</sup> C tolerable spike time	0	50	0	50	ns
$t_{\rm sds}$	I <sup>2</sup> C serial data setup time	250		250		ns
$t_{sdh}$	I <sup>2</sup> C serial data hold time	0		0		μs
t <sub>icr</sub> (2)	I <sup>2</sup> C input rise time		1000		300	ns
$t_{icf}^{(2)}$	I <sup>2</sup> C input fall time		300		300	ns
t <sub>ocf</sub> (2)	I <sup>2</sup> C output fall time; 10 pF to 400 pF bus		300		300	ns
$t_{buf}$	I <sup>2</sup> C bus free time between Stop and Start	4.7		1.3		μs
t <sub>sts</sub>	I <sup>2</sup> C Start or repeated Start condition setup time	4.7		0.6		μs
t <sub>sth</sub>	I <sup>2</sup> C Start or repeated Start condition hold time	4		0.6		μs
t <sub>sps</sub> (2)	I <sup>2</sup> C Stop condition setup time	4		0.6		μs

<sup>(1)</sup> The I<sup>2</sup>C interface will operate in either standard or fast mode.

<sup>(2)</sup> Parameters not tested in production.



#### **FUNCTIONAL DESCRIPTION**

The TS52003 is a fully-integrated super capacitor charger IC based on a highly-efficient switching topology. It includes a Maximum Power Point Tracking (MPPT) function to optimize its input voltage to extract the maximum possible power from a photovoltaic cell. It includes configurability for termination voltage and charge current. A 1 MHz internal switching frequency facilitates low-cost LC filter combinations.

When enabled, the TS52003 will provide the maximum power available from a photovoltaic cell until the output voltage reaches the termination point. At that point, it will begin to regulate voltage. It will do so until a fault is detected, it is disabled or the output voltage drops below the termination point.

#### INTERNAL PROTECTION DETAILS

#### **Internal Current Limit**

The current through the inductor is sensed on a cycle by cycle basis and if current limit is reached, it will abbreviate the cycle. Current limit is always active when the regulator is enabled.

#### **Thermal Shutdown**

If the temperature of the die exceeds 170C (typical), the SW outputs will tri-state to protect the device from damage. The nFLT and all other protection circuitry will stay active to inform the system of the failure mode. Once the device cools to 160C (typical), the device will attempt to start up again. If the device reaches 170C, the shutdown/restart sequence will repeat.

#### **VIN Under-Voltage Lockout**

The device is held in the off state until VIN reaches 3.15V. There is a 200mV hysteresis on this input, which requires the input to fall below 2.95V before the device will disable.

#### **VOUT Over-Voltage Protection**

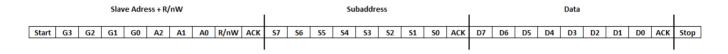
The TS52003 has an output protection circuit designed to shutdown the charging profile if the output voltage is greater than the termination voltage. The termination voltage can change based on user programming, so the protection threshold is set to 2% above the termination voltage. Shutting down the charging profile puts the TS52003 in a fault condition.



#### SERIAL INTERFACE

The TS52003 features an I²C slave interface which offers advanced control and diagnostic features. I²C operation offers configuration control for termination voltages, charge currents, and charge timeouts. I²C operation also offers fault and warning indicators. Whenever a fault is detected, the associated status bit in the STATUS register is set and the nFLT pin is pulled low. Whenever a warning is detected, the associated status bit in the STATUS register is set, but the nFLT pin is not pulled low. Reading of the STATUS register resets the fault and warning status bits, and the nFLT pin is released after all fault status bits have been reset.

### I<sup>2</sup>C SUBADDRESS DEFINITION



Start - Start Condition

G(3:0) - Group ID: Address fixed at 1001b A(2:0) - Device ID: Address fixed at 000b R/nW - Read / not Write select bit ACK - Acknowledge

S(7:0) - Subaddress: Defined per the address register map D(7:0) - Data: Data to be transmitted with the device

Stop - Stop Condition

Figure 3: Sub-address in I<sup>2</sup>C Transmission

### I<sup>2</sup>C BUS OPERATION

The TS52003 has a slave I<sup>2</sup>C interface that supports standard and fast mode data rates, auto-sequencing, and is compliant to I<sup>2</sup>C standard version 3.0.

I<sup>2</sup>C is a two-wire serial interface where the two lines are serial clock (SCL) and serial data (SDA). SDA must be connected to a positive supply through an external pull-up resistor. The devices communicating on this bus can drive the SDA line low or release it to high impedance. The device that initiates the I<sup>2</sup>C transaction becomes the master of the bus. Communication is initiated by the master sending a Start condition, a high-to-low transition on SDA, while the SCL line is high. After the Start condition, the device address byte is sent, most significant bit (MSB) first, including the data direction bit (R/nW). After receiving the valid address byte, the device responds with an acknowledge (ACK). An ACK is a low on SDA during the high of the ACK related clock pulse. On the I<sup>2</sup>C bus, during each clock pulse only one data bit is transferred. The data on the SDA line must remain stable during the high pulse of the clock period, as changes in the data line at this time are interpreted as Start or Stop control commands. A low-to-high transition on SDA while the SCL input is high indicates a Stop condition and is sent by the master (see Figure 4).

Any number of data bytes can be transferred from the transmitter to receiver between the Start and the Stop conditions. Each byte of eight bits is followed by one ACK bit. The SDA line must be released by the transmitter before the receiver can send an ACK bit. The receiver that acknowledges must pull down the SDA line during the ACK clock pulse, so that the SDA line is stable low during the high pulse of the ACK-related clock period. When a slave receiver is addressed, it must generate an ACK after each byte is received. Similarly, the master must generate an ACK after each byte that it receives from the slave transmitter. To ensure proper operation, setup and hold times must be met. An end of data is signaled by the master receiver to the slave transmitter by not generating an acknowledge after the last byte has been clocked out of the slave. This is done by the master receiver by holding the SDA line high. The transmitter must then release the data line to enable the master to generate a Stop condition.

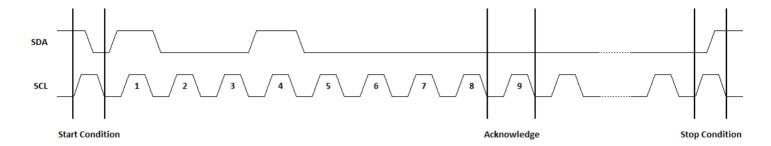


Figure 4: I<sup>2</sup>C Start / Stop Protocol

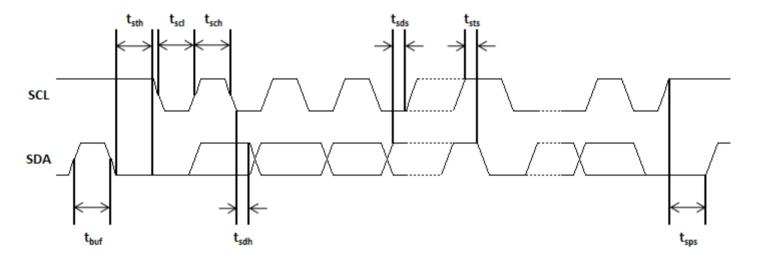


Figure 5: I<sup>2</sup>C Data Transmission Timing



REGISTER DESCRIPTION (Device Address = 0x48)

REGISTER	ADDRESS (HEX)	NAME	DEFAULT	DESCRIPTION
0	00	STATUS	0x00	Status bit register
1	N/A	N/A	N/A	Register not implemented
2	02	CONFIG1(1)	EEPROM	Configuration register
3	N/A	N/A	N/A	Register not implemented
4	04	CONFIG3(1)	EEPROM	Configuration register
5-16	N/A	N/A	N/A	Registers not implemented
17	11	CONFIG_ENABLE	0x00	Enable configuration register access
18	12	EEPROM_CTRL(1)	0x00	EEprom control register

<sup>(1)</sup> CONFIG and EEPROM\_CTRL registers are only accessible when CONFIG\_ENABLE register is written.

## **STATUS REGISTER (STATUS)**

Address - 0x00h

DATA BIT	D7	D6	D5	D4	D3	D2	D1	D0
FIELD NAME	VOUT_OV	Not Used	Not Used	Not Used	TSD	Not Used	VIN_UV	Not Used
READ/WRITE	R	R	R	R	R	R	R	R

FIELD NAME	BIT DEFINITION <sup>(2)</sup>
VOUT_OV	Vout over-voltage
TSD	Thermal shutdown
VIN_UV	VIN under-voltage

<sup>(1)</sup> Fault is defined as VOUT\_OV. Warnings are defined as TSD, and VIN\_UV. Faults cause the nFLT pin to be pulled low, Warnings do not cause the nFLT pin to be pulled low. All status bits are cleared after register read access. nFLT pin will go high impedance (open drain output) after the status register has been read and all status bits have been reset.



# **CONFIGURATION REGISTER (CONFIG1)**

Address - 0x02h

DATA BIT	D7	D6	D5	D4	D3	D2	D1	D0
FIELD NAME	Not	Used	V_TERM [2:0]		Not Used			
READ/WRITE	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

FIELD NAME	BIT DEFINITION
V_TERM [2:0]	Voltage Termination configuration
	000 - 2.48 V
	001 – 2.54 V
	010 - 2.60 V
	011 - 2.66 V
	100 – 2.68 V
	101 – 2.72 V
	110 – 2.74 V
	111 – (Factory use only)

# **CONFIGURATION REGISTER (CONFIG3)**

Address - 0x04h

DATA BIT	D7	D6	D5	D4	D3	D2	D1	D0
FIELD NAME	MAX_CHRG_CURR [3:0]			Not Used				
READ/WRITE	R/W R/W R/W R/W				R/W	R/W	R/W	R/W

FIELD NAME	BIT DEFINITION
MAX_CHRG_CURR[3:0]	Maximum charge current configuration
	0000 – 50 mA
	0001 – 100 mA
	0010 – 200 mA
	0011 – 300 mA
	0100 – 400 mA
	0101 – 500 mA
	0110 – 600 mA
	0111 – 700 mA
	1000 – 800 mA
	1001 – 900 mA
	1010 – 1000 mA
	1011 – 1100 mA
	1100 – 1200 mA
	1101 – 1300 mA
	1110 – 1400 mA
	1111 – 1500 mA



# ENABLE CONFIGURATION REGISTER (CONFIG\_ENABLE)

Address – 0x11h

DATA BIT	D7	D6	D5	D4	D3	D2	D1	D0
FIELD NAME	Not used	EN_CFG						
READ/WRITE	R	R	R	R	R	R	R	R/W
RESET VALUE	0	0	0	0	0	0	0	0

FIELD NAME	BIT DEFINITION
EN_CFG	Enable access control bit for configuration registers 2 and 4
	0 – Disable access
	1 – Enable access

## EEPROM CONTROL REGISTER (EEPROM\_CTRL)

Address - 0x12h

DATA BIT	D7	D6	D5	D4	D3	D2	D1	D0
FIELD NAME	Not used	EE_PROG						
READ/WRITE	R	R	R	R	R	R	R	R/W
RESET VALUE	0	0	0	0	0	0	0	0

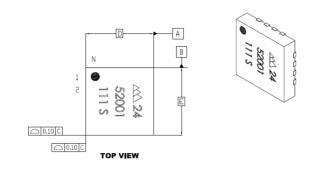
FIELD NAME	BIT DEFINITION	
EE_PROG <sup>(1)</sup>	EEPROM program control bit for configuration registers 2 and 4	
	0 - Disable EEPROM programming	
	1 – Enable EEPROM programming with data from configuration registers 2 and 4	

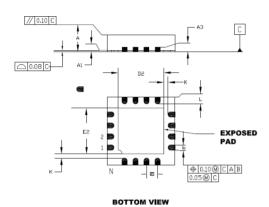
<sup>(1)</sup> EE\_PROG Note: Inputs VIN and EN must be present for 200ms.

#### EXTERNAL COMPONENT SELECTION

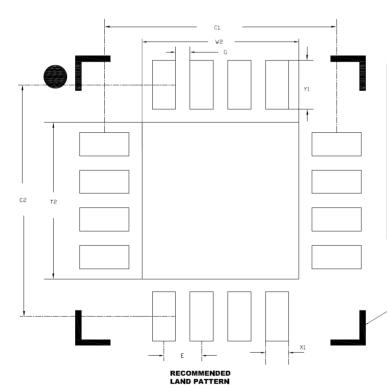
The internal compensation is optimized for a 4.7uF output capacitor and a 4.7uH inductor. To keep the output ripple low, a low ESR (less than 35mOhm) ceramic is recommended.

### PACKAGE MECHANICAL DRAWINGS





Units MILLIMETERS Dimensions Limits MIN NOM MAX Number of Pins Ν 16 Pitch 0.65 BSC Overall Height 0.80 0.90 1.00 Α Standoff Α1 0.00 0.02 0.05 Contact Thickness А3 0.20 REF Overall Length 4.00 BSC D Exposed Pad Width E2 2.55 2.80 2.70 Overall Width Ε 4.00 BSC 2.80 Exposed Pad Length D2 2.55 2.70 Contact Width b 0.25 0.30 0.35 Contact Length 0.30 0.50 Contact-to-Exposed Pad 0.20 К



	Units	N	/ILLIMETER	S
Dimens	MIN	NOM	MAX	
Contact Pitch	Е		0.65 BSC	
Optional Center Pad Width	W2	-	-	2.70
Optional Center Pad Length	T2	-	-	2.70
Contact Pad Spacing	C1	-	4.00	-
Contact Pad Spacing	C2	-	4.00	-
Contact Pad Width (X16)	X1	-	-	0.40
Contact Pad Length (X16)	Y1	-	-	0.85
Distance Between Pads	G	0.25	-	-

#### Notes:

Silk Screem

Dimensions and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

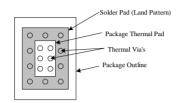
REF: Refernce Dimension, usually without tolerance, for information only.



#### APPLICATION USING A MULTI-LAYER PCB

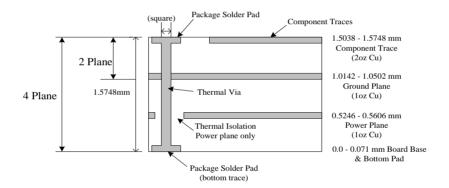
To maximize the efficiency of this package for application on a single layer or multi-layer PCB, certain guidelines must be followed when laying out this part on the PCB.

The following are guidelines for mounting the exposed pad IC on a Multi-Layer PCB with ground a plane.



Package and PCB Land Configuration For a Multi-Layer PCB

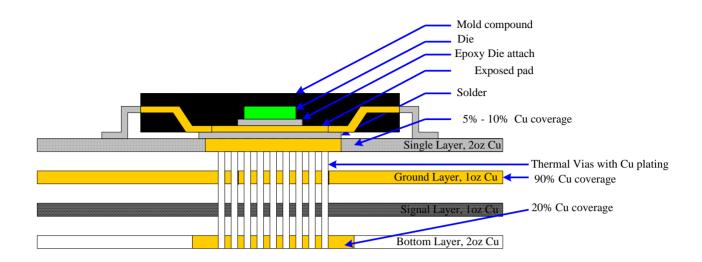
#### **JEDEC standard FR4 PCB Cross-section:**



Multi-Layer Board (Cross-sectional View)

In a multi-layer board application, the thermal vias are the primary method of heat transfer from the package thermal pad to the internal ground plane. The efficiency of this method depends on several factors, including die area, number of thermal vias, thickness of copper, etc.

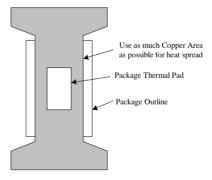




Note: NOT to Scale

The above drawing is a representation of how the heat can be conducted away from the die using an exposed pad package. Each application will have different requirements and limitations and therefore the user should use sufficient copper to dissipate the power in the system. The output current rating for the linear regulators may have to be de-rated for ambient temperatures above 85C. The de-rate value will depend on calculated worst case power dissipation and the thermal management implementation in the application.

#### APPLICATION USING A SINGLE LAYER PCB



Layout recommendations for a Single Layer PCB: utilize as much Copper Area for Power Management. In a single layer board application the thermal pad is attached to a heat spreader (copper areas) by using low thermal impedance attachment method (solder paste or thermal conductive epoxy).

In both of the methods mentioned above it is advisable to use as much copper traces as possible to dissipate the heat.

#### **IMPORTANT:**

If the attachment method is NOT implemented correctly, the functionality of the product is not guaranteed. Power dissipation capability will be adversely affected if the device is incorrectly mounted onto the circuit board.



#### **Legal Notices**

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